

METHOD FOR MANUFACTURING NITRIDE LIGHT-EMITTING DEVICE

ABSTRACT OF THE DISCLOSURE

A method for manufacturing nitride light-emitting device is disclosed, which fixes two metallic bonding layers together in order to bond a nitride lighting structure grown on a poor thermal conductivity substrate to a high thermal conductivity substrate, then removes the poor thermal conductivity substrate by means of chemical etching, dry etching, or mechanical abrading to thereby transfer the nitride lighting structure onto that high thermal conductivity substrate. Meanwhile, by taking advantage of forming ohmic contact between a transparent conductive layer and an N-type nitride epitaxial layer, the uniformity of current distribution can be significantly improved to thereby suppress light absorption effect and heighten the lighting efficiency of the light emitting device.